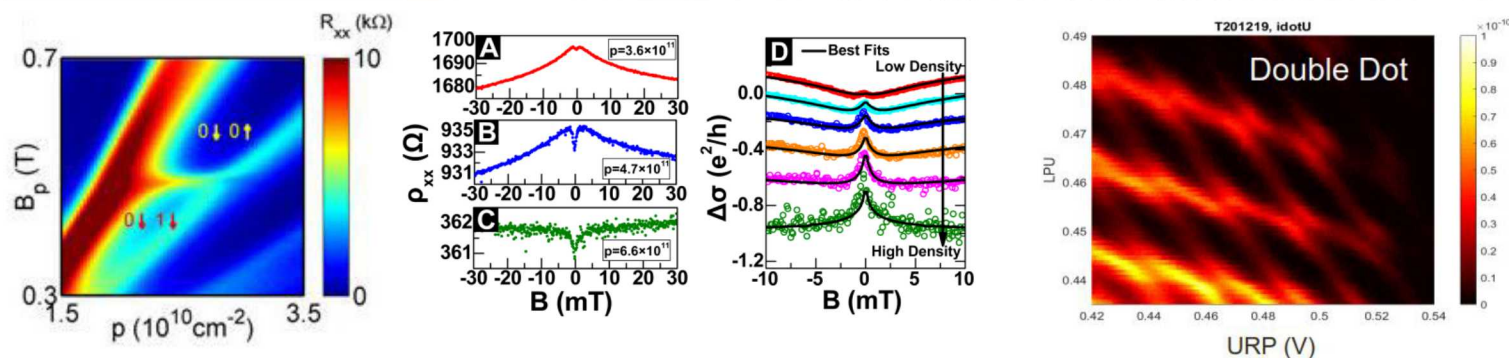




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SAND2019-1752PE

Ge/SiGe quantum electronic devices



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Acknowledgements

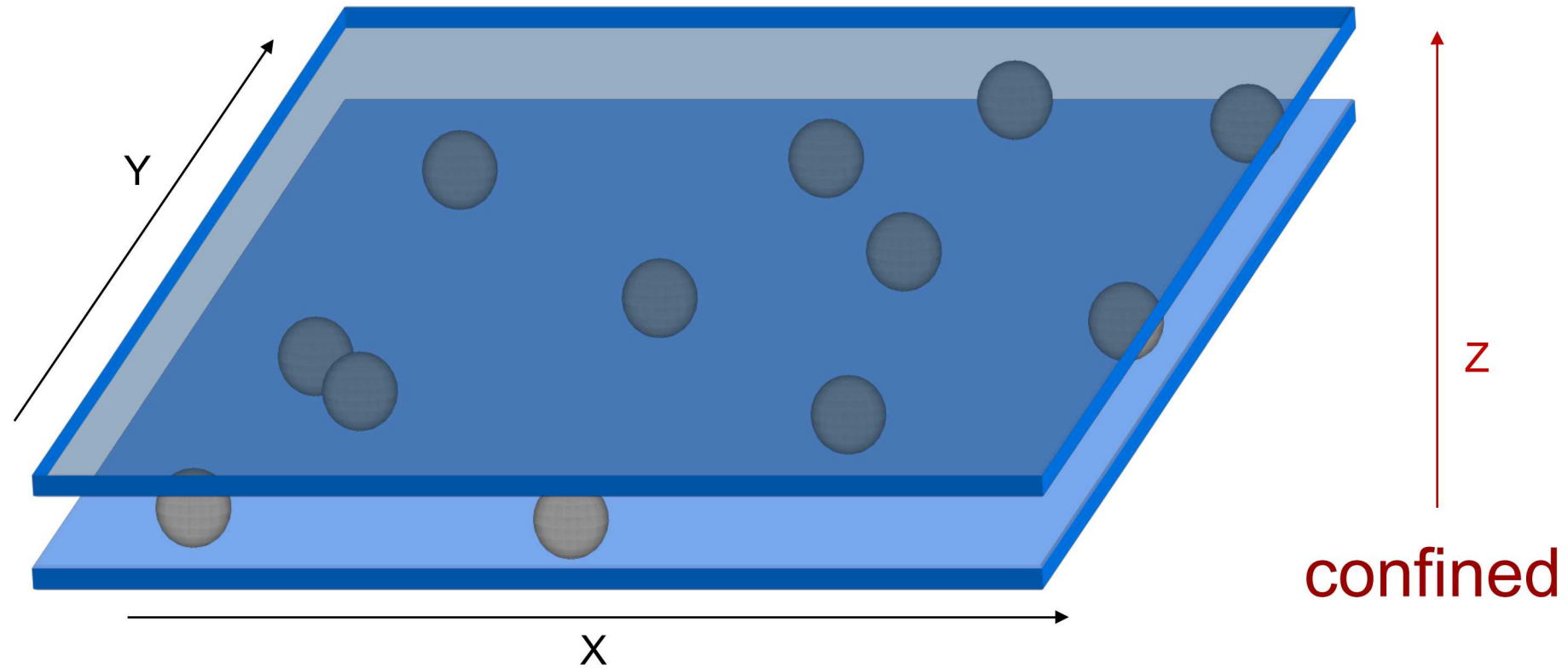
- Sandia National Laboratories: M. P. Lilly, D. Laroche, L. A. Tracy, C. T. Harris, N. T. Jacobson, J. Moussa, A. D. Baczewski, D. R. Luhman, W. Hardy, and L. N. Maurer.
- National Taiwan University: C. W. Liu, J.-Y. Li, C.-H. Lee, S.-H. Huang, Y. Chuang, Y.-H. Su, C.-T. Chou
- NHMFL

This work at Sandia National Laboratories has been supported by the Division of Materials Sciences and Engineering, Office of Basic Energy Sciences, U.S. Department of Energy (DOE) and the Laboratory Directed Research and Development Program. This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S. DOE, Office of Basic Energy Sciences, user facility. Sandia National Laboratories is a multi-mission laboratory managed and operated by National Technology and Engineering Solutions of Sandia, LLC., a wholly owned subsidiary of Honeywell International, Inc., for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA-0003525. The views expressed in this presentation do not necessarily represent the views of the U.S. Department of Energy or the United States Government.

Outline

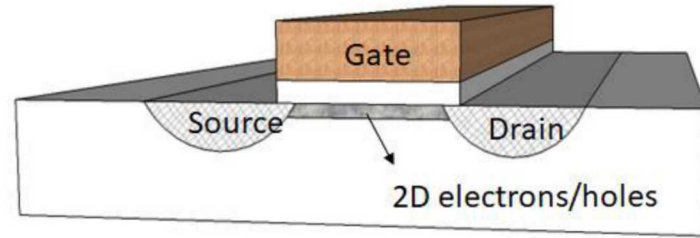
- Ge/SiGe heterostructures
- Device operation
- Properties of 2D holes in Ge/SiGe
- Quantum Hall ferromagnetic transition
- Spin qubits in Ge/SiGe
- Summary

2D electrons/holes

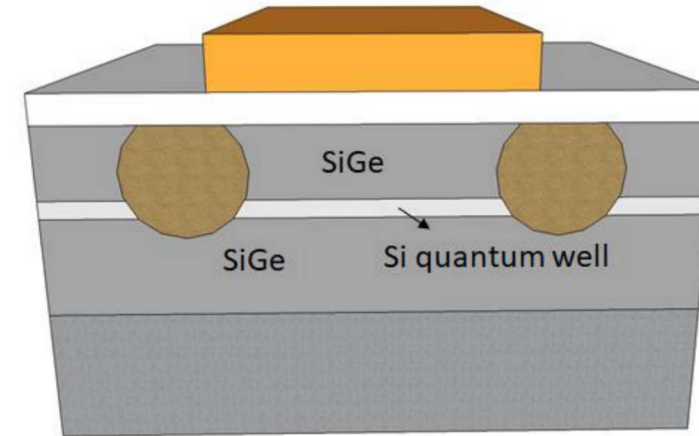


2D electrons in Si

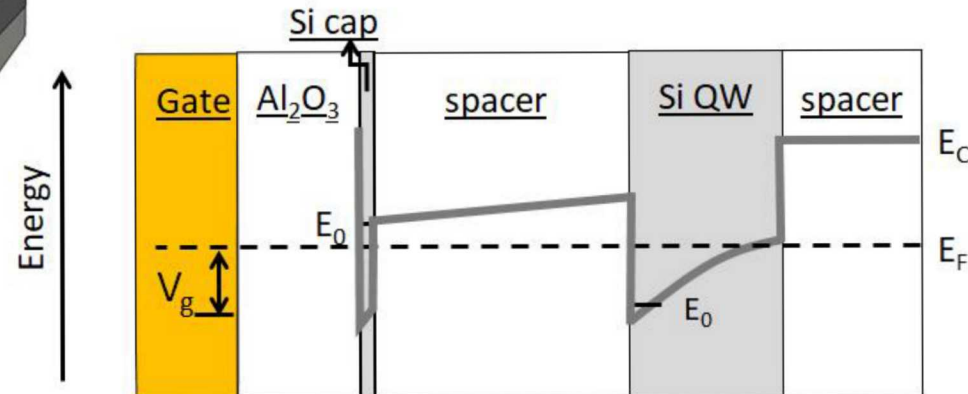
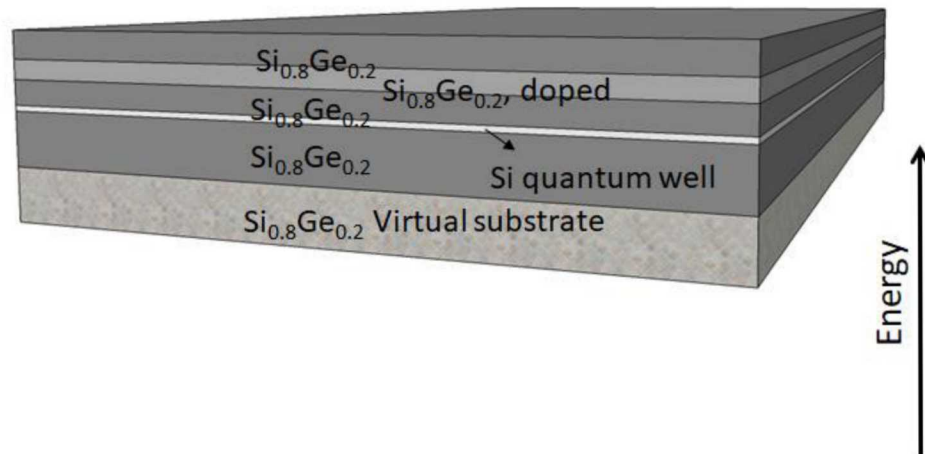
Si MOSFET



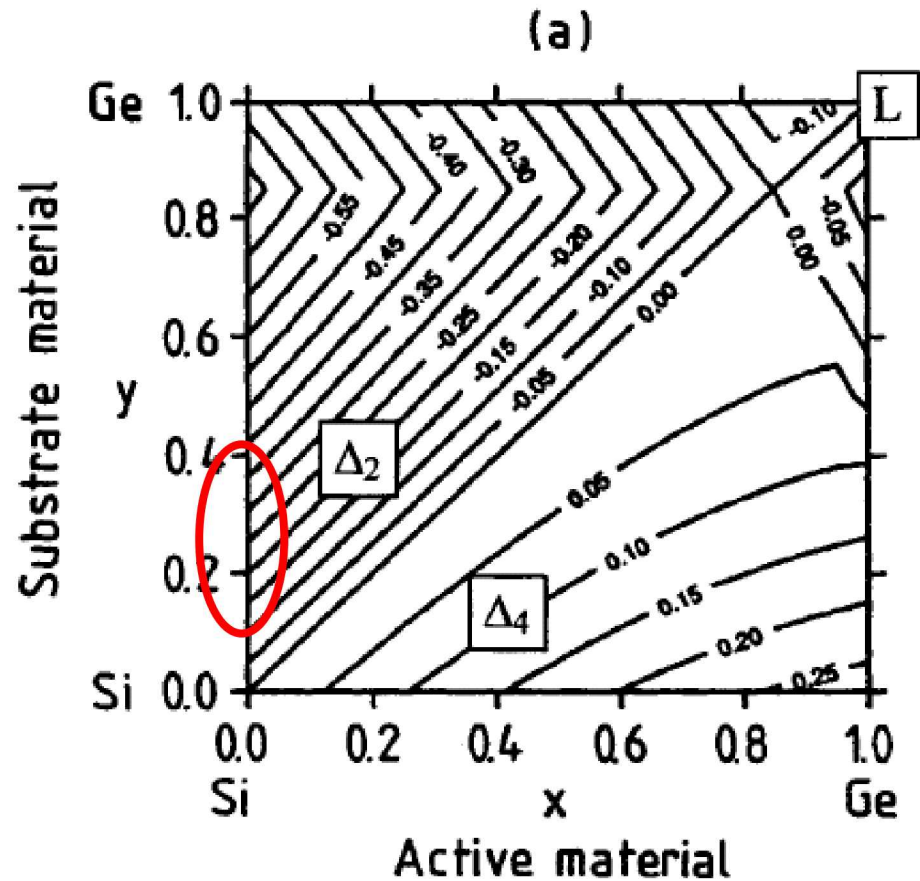
Undoped Si/SiGe HFET



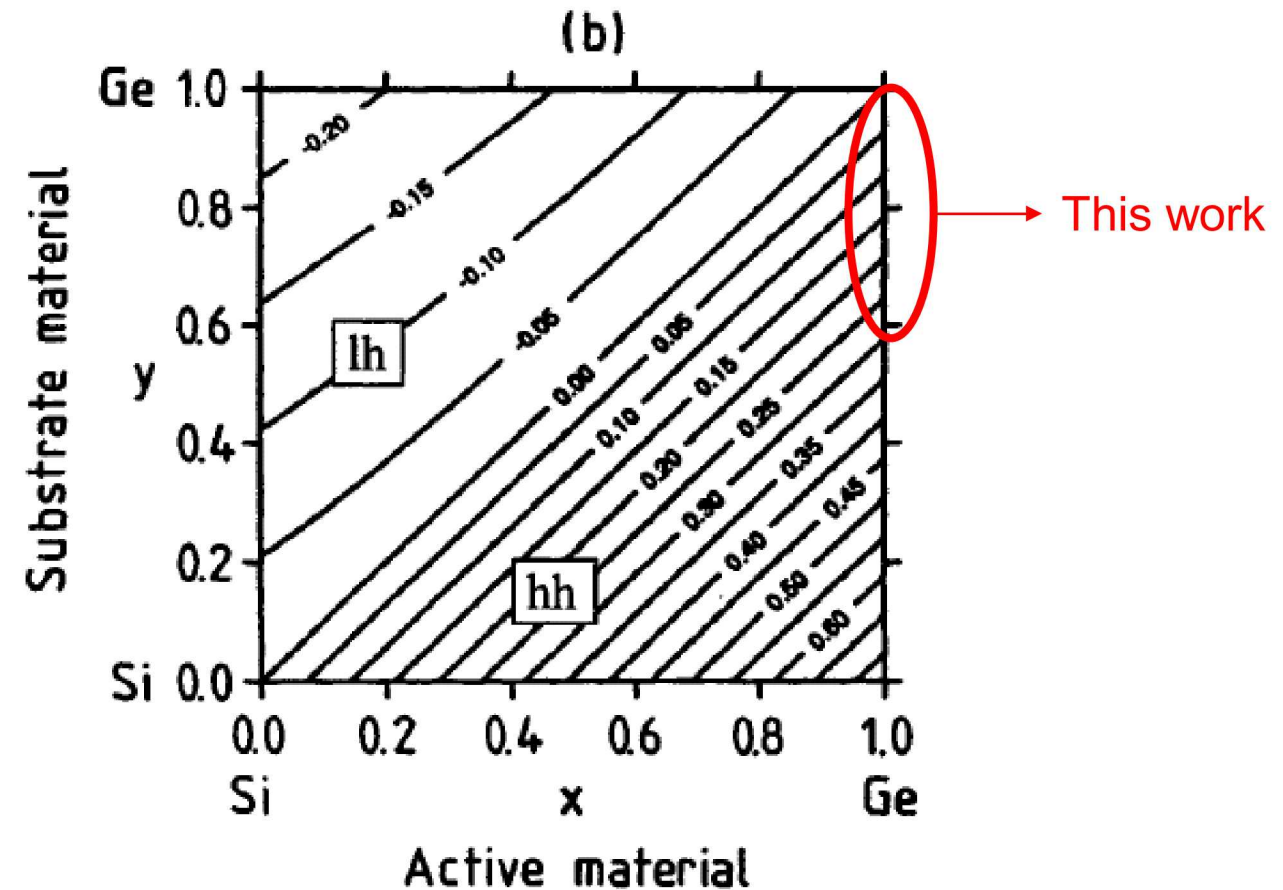
Modulation doped Si/SiGe



Band alignment of SiGe heterostructures

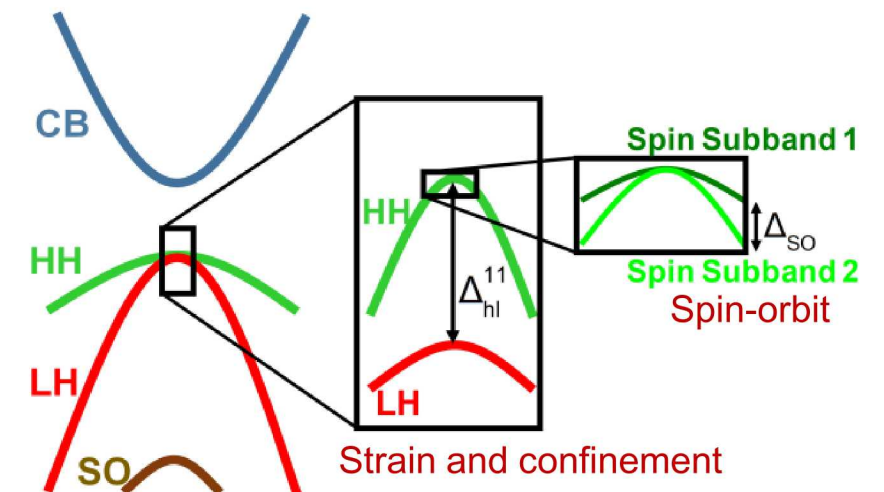
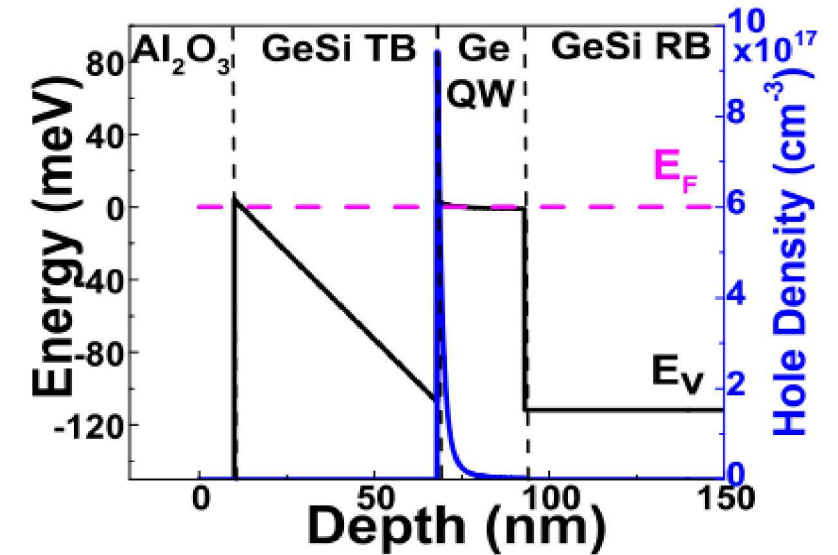
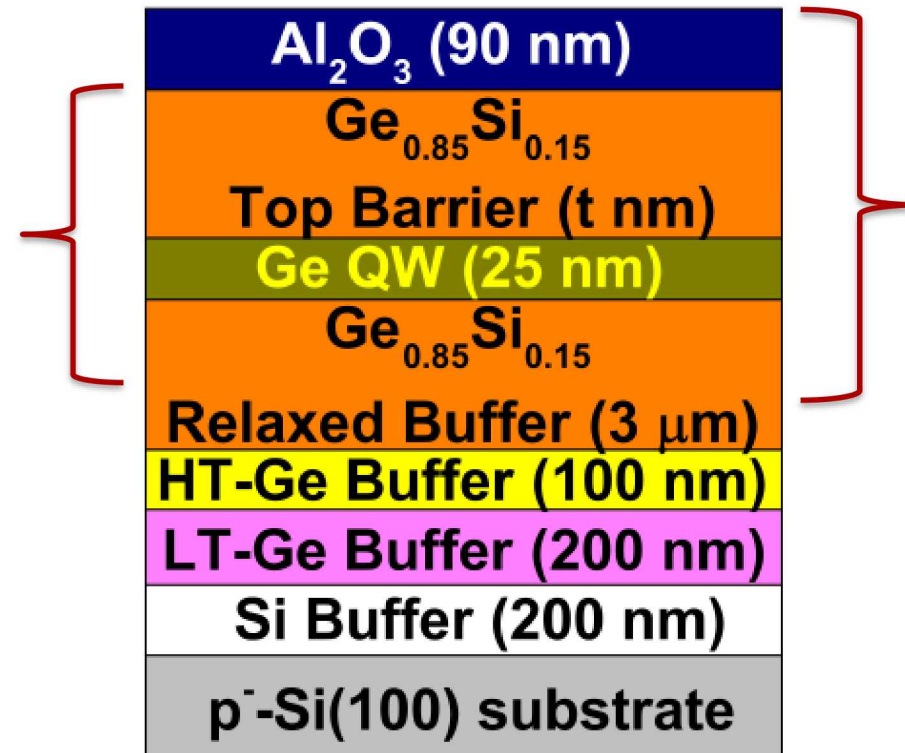
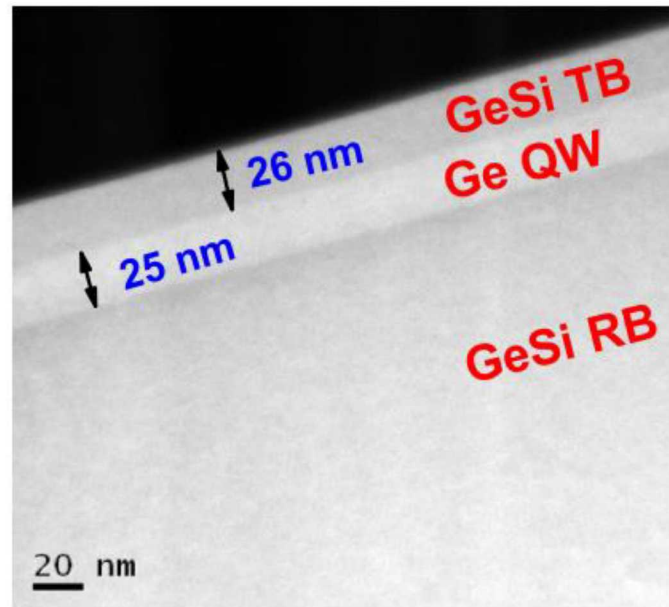


Conduction band
2D electrons in Si quantum wells



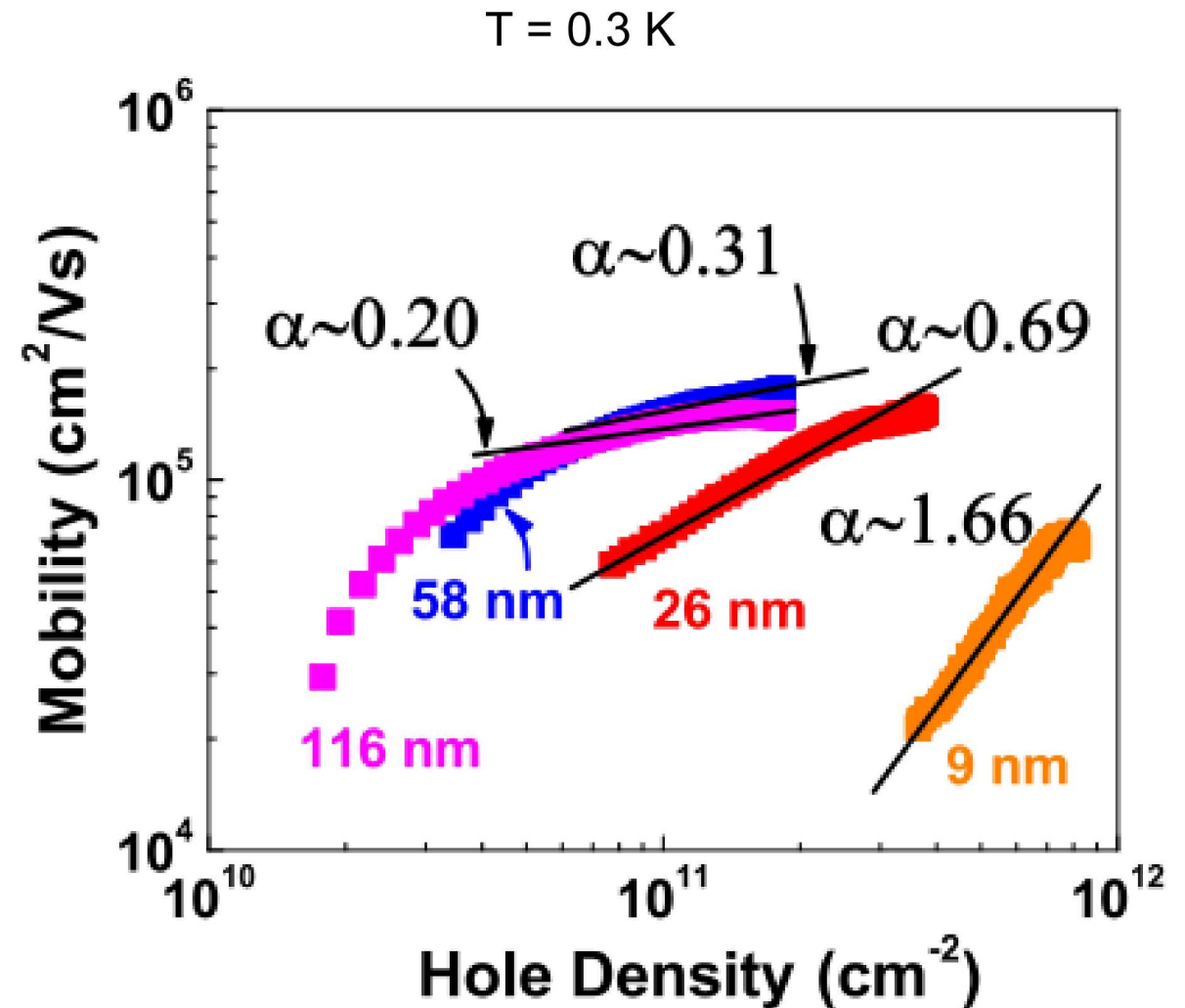
Valance band
2D holes in Ge quantum wells

Undoped Ge/SiGe heterostructure field-effect transistors



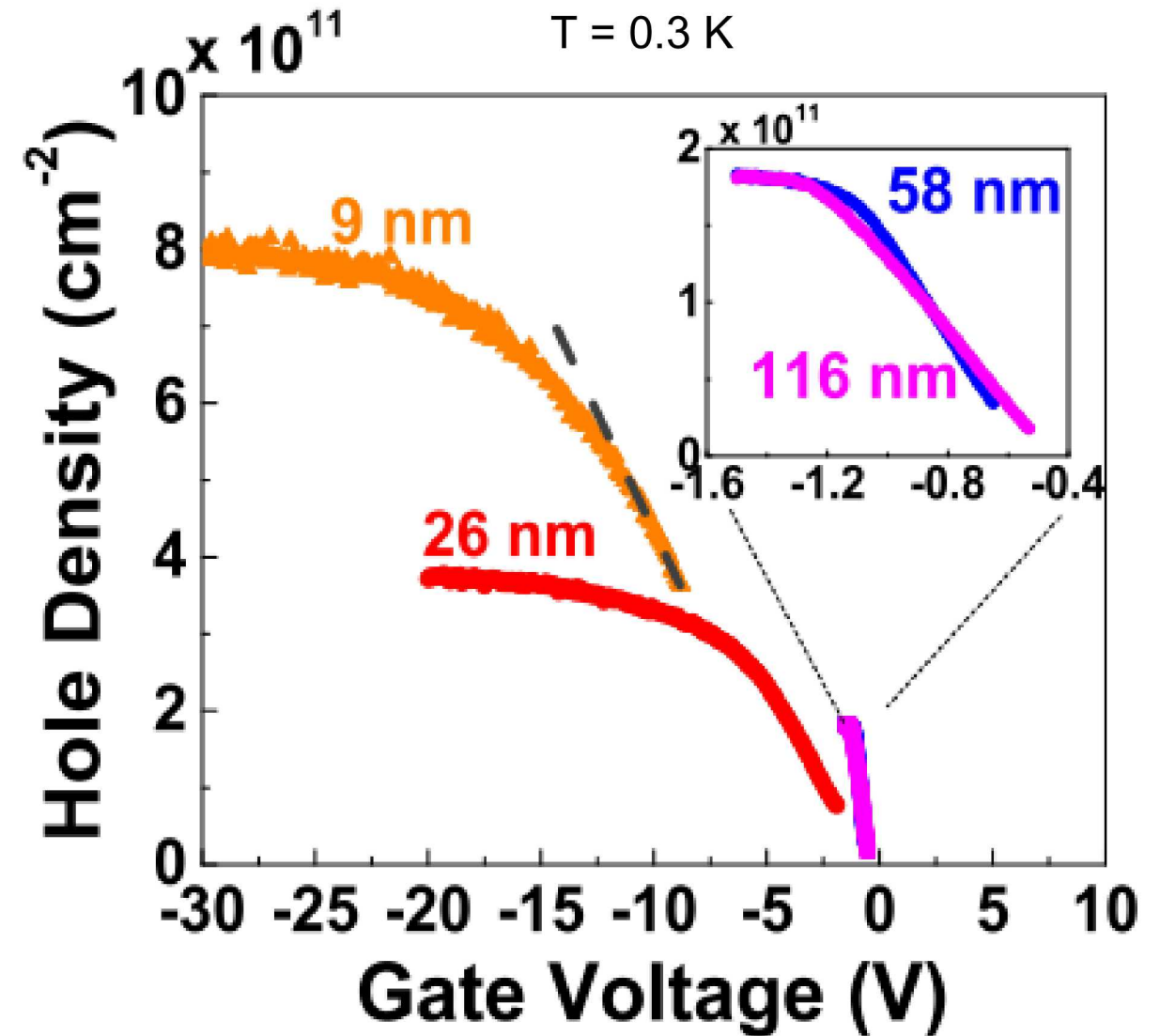
Device operation – mobility

- Mobility on the order of $2 \times 10^5 \text{ cm}^2/\text{Vs}$ achievable
- Mobility increases with density
=> screening
- Shallower channels have lower mobilities
=> oxide/GeSi interface is disordered

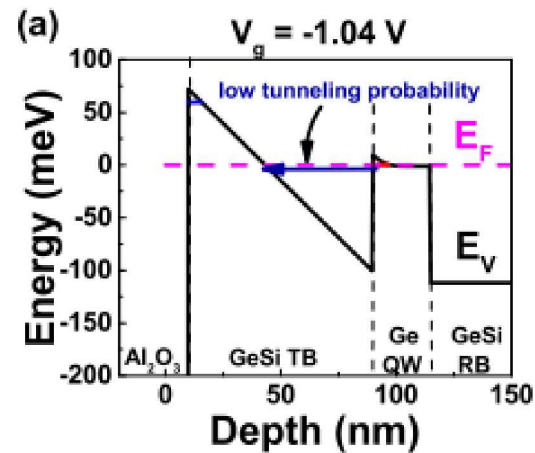


Device operation – 2D hole density

- The 2D hole density saturates.
- Shallow channels
 - High saturation densities, depth dependent.
 - Small slopes (capacitances)
- Deep channels
 - Low saturation densities, depth independent.
 - Large slopes (capacitances)



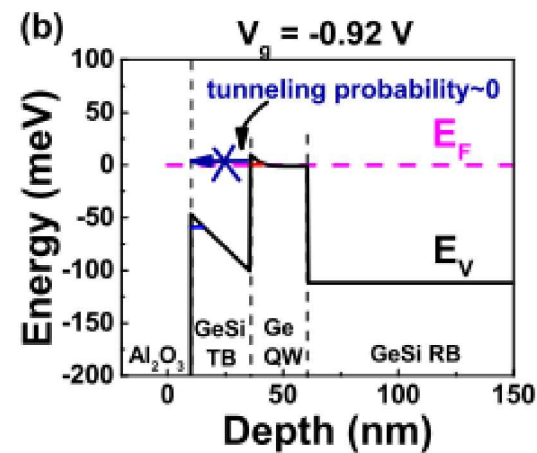
Device operation – 2D hole density



Deep channels

The tunnel rate is limited by triangular barrier (set by Si%) and is depth independent.

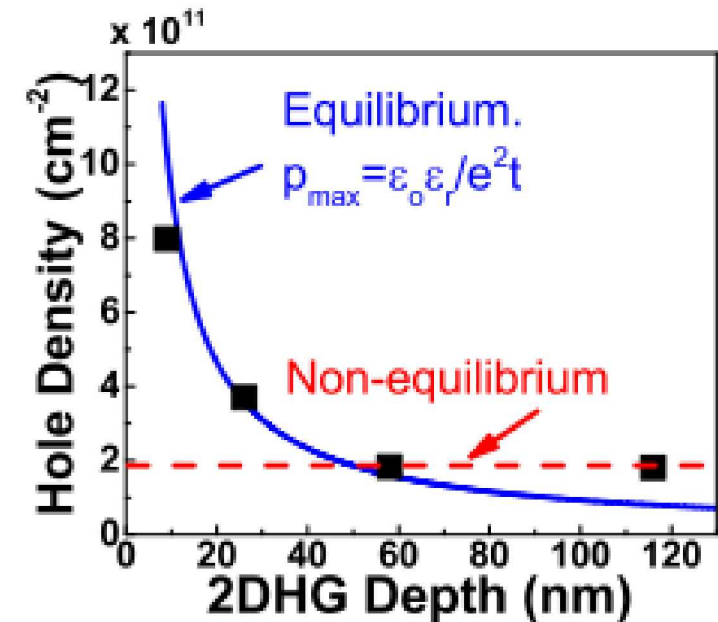
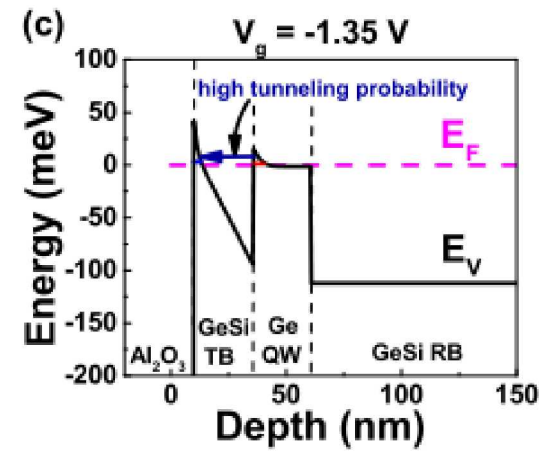
The tunnel rate can be so low that the density only slowly decreases and never reaches equilibrium at low temperatures!



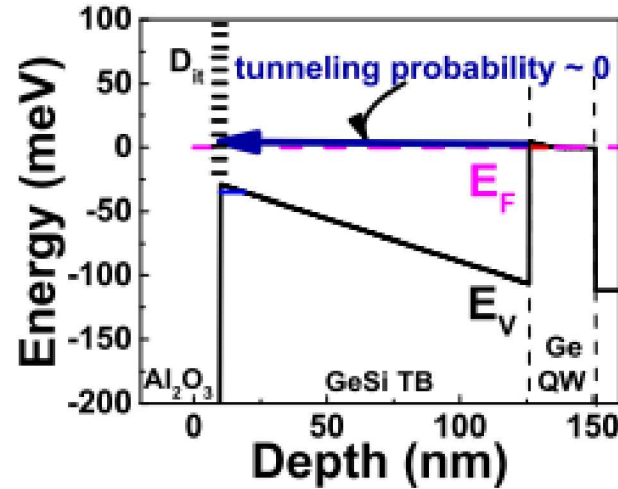
Shallow channels

The tunneling rate is high (compared to experiment time scales).

The density probed by the Hall effect approaches the equilibrium case.



Device operation – 2D hole density

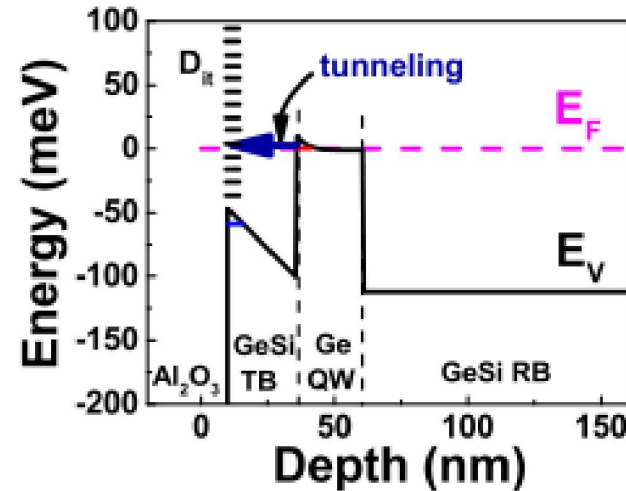


Deep channels

The tunnel rate is low.

The traps at the oxide/GeSi interface do not (need to) get filled.

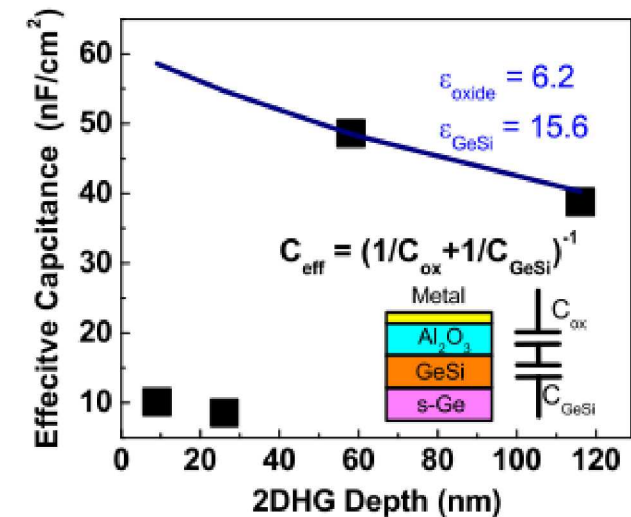
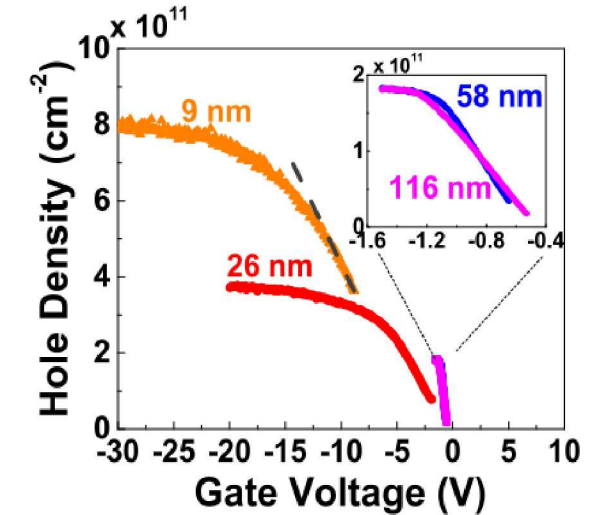
$$C_{\text{eff}} \sim C_{\text{geometric}}$$



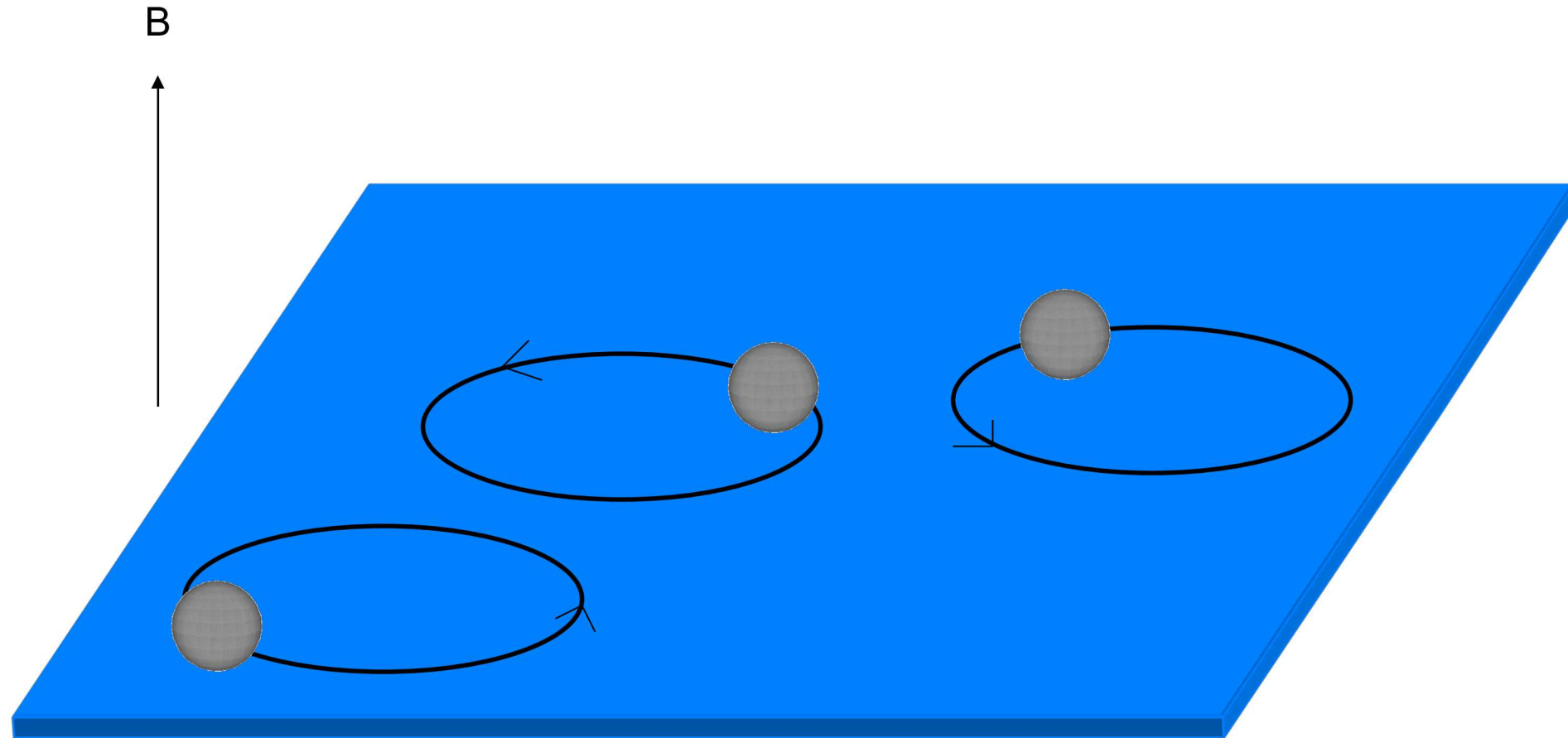
Shallow channels

The tunnel rate is high.

The traps at the oxide/GeSi interface need to be filled before the Fermi level can move.



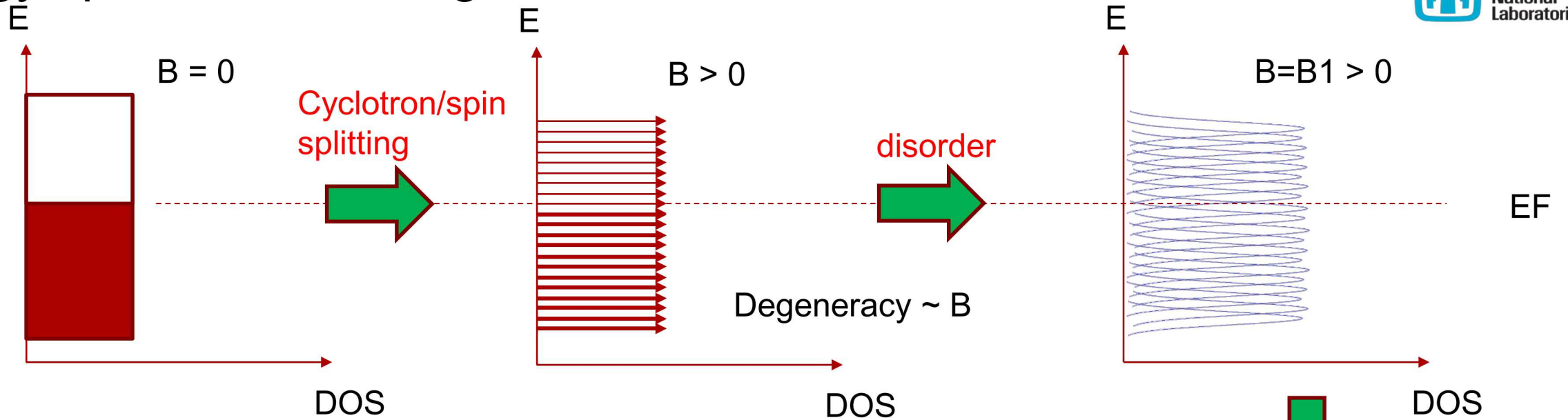
In a perpendicular magnetic field...



Cyclotron motion, $E_c = \hbar e B_{\text{perp}} / m^*$

Spin splitting, gap $E_z = g \mu B_{\text{total}}$

Energy spectrum in a magnetic field



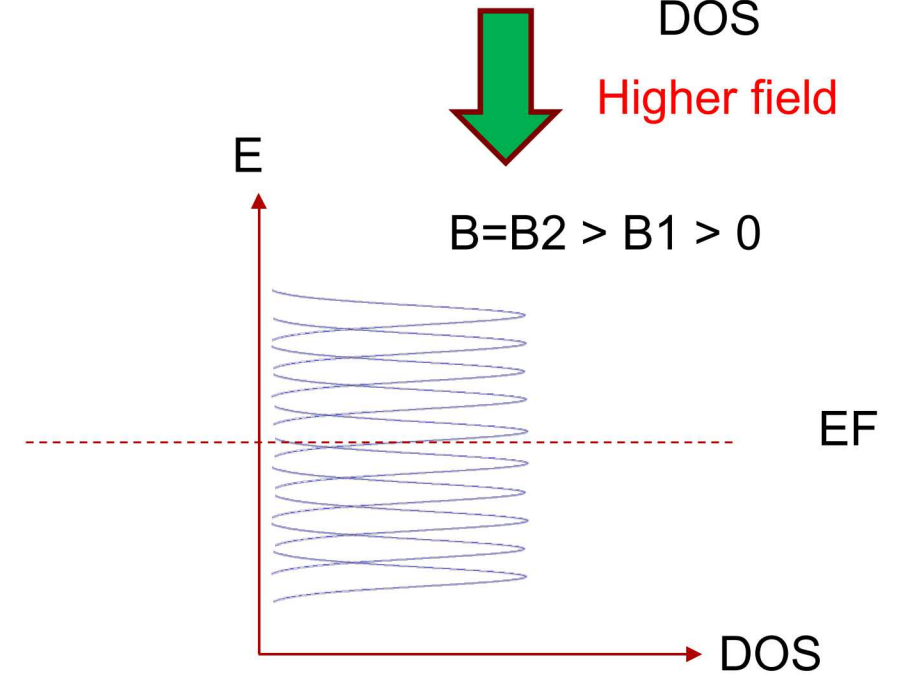
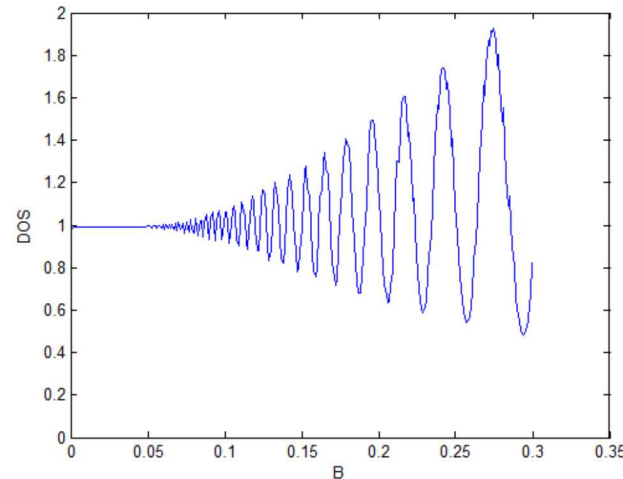
$$\frac{\Delta \rho}{\rho_0} \sim D(X) \frac{\Delta DOS}{DOS}$$

$$D(X) = X / \sinh X$$

$$X = 2\pi kT / \text{Gap}$$

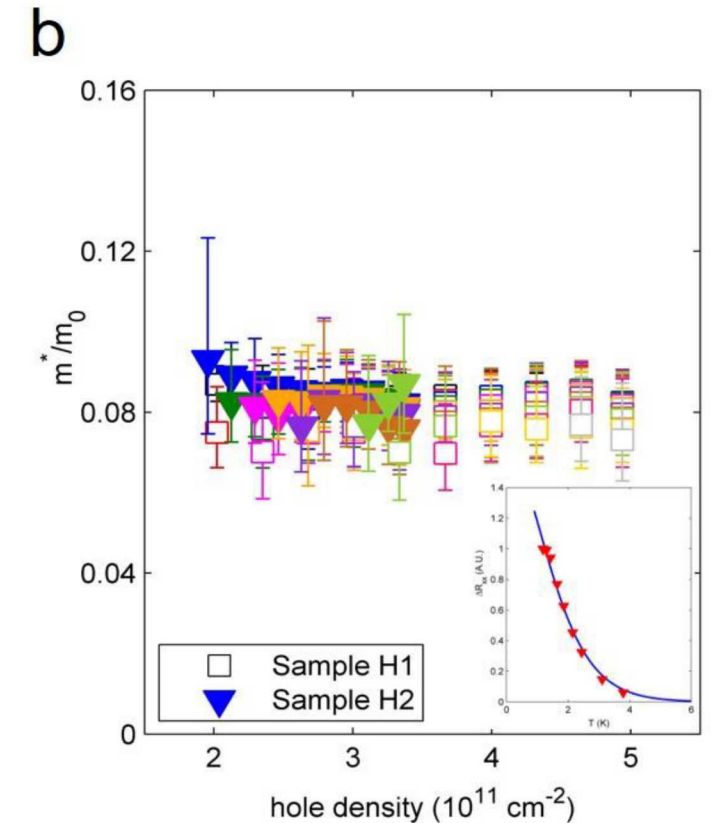
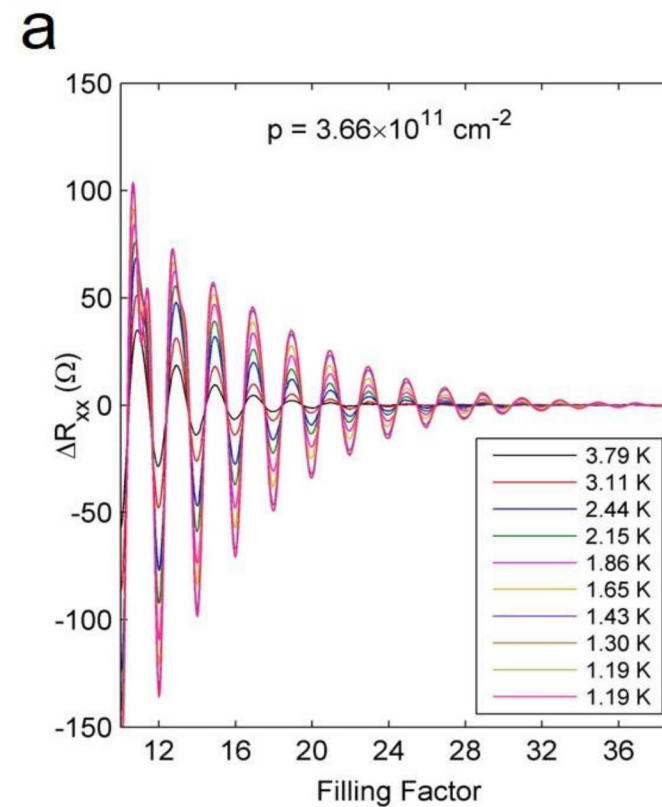
Temperature dependence
 $\Leftrightarrow$ Gap measurement
 $\Leftrightarrow$ cyclotron gap or spin gap

DOS at Fermi energy at a fixed density



Physical properties – effective mass (even filling factors)

- $\sim 0.08 m_0$.
- $\sim$ density independent.
- This mass is small compared to the mass of electrons in Si (0.19), the mass of holes in GaAs (0.2-0.4), and is comparable to the mass of electrons in GaAs (0.07).
- Smaller mass
=> more extended wave functions
=> easier gate controls for nanostructures



Physical properties – effective mass (even filling factors)

Theory

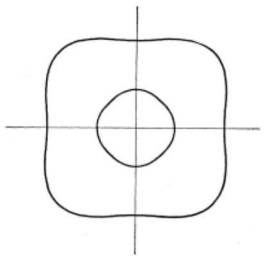
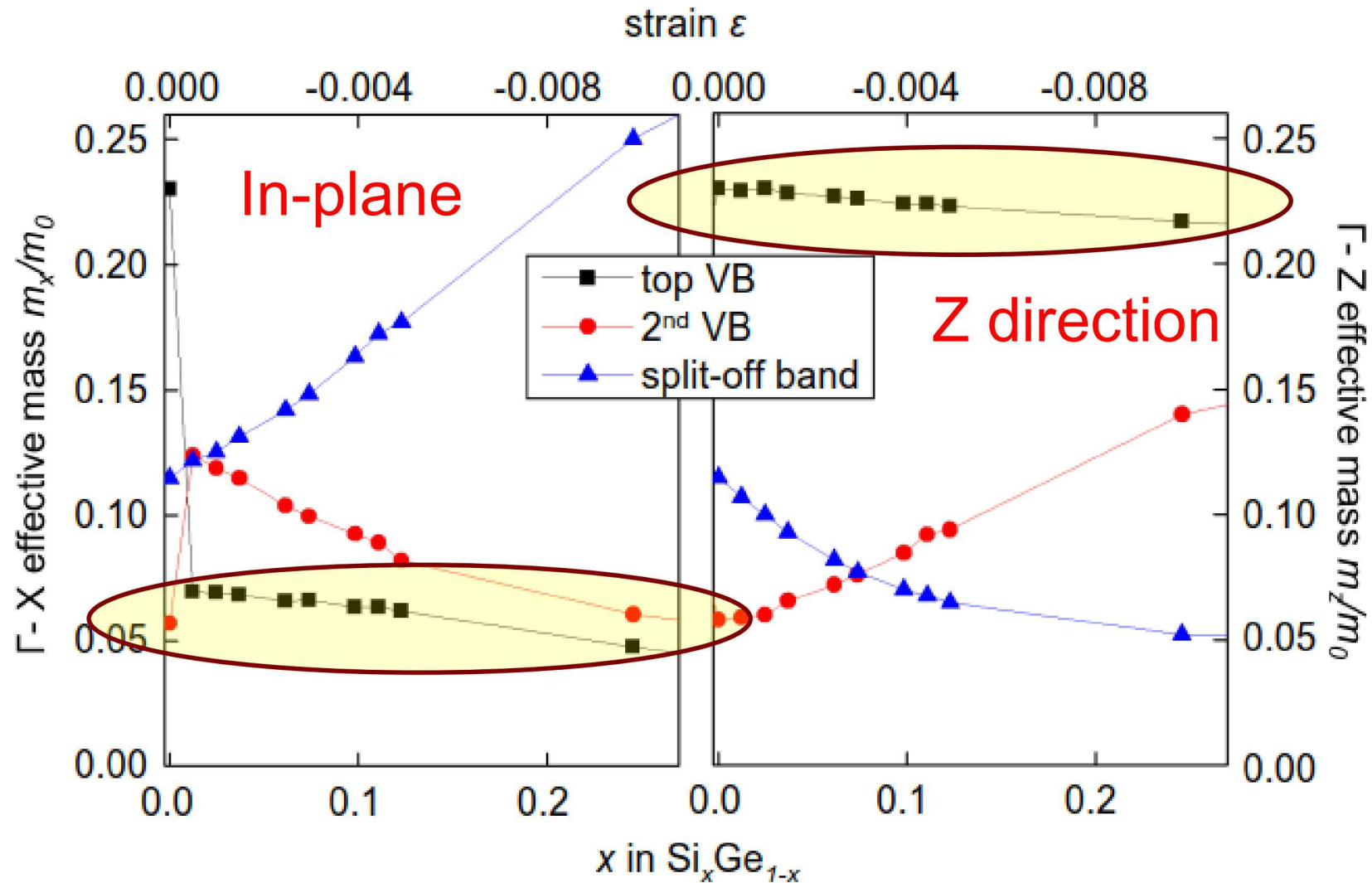
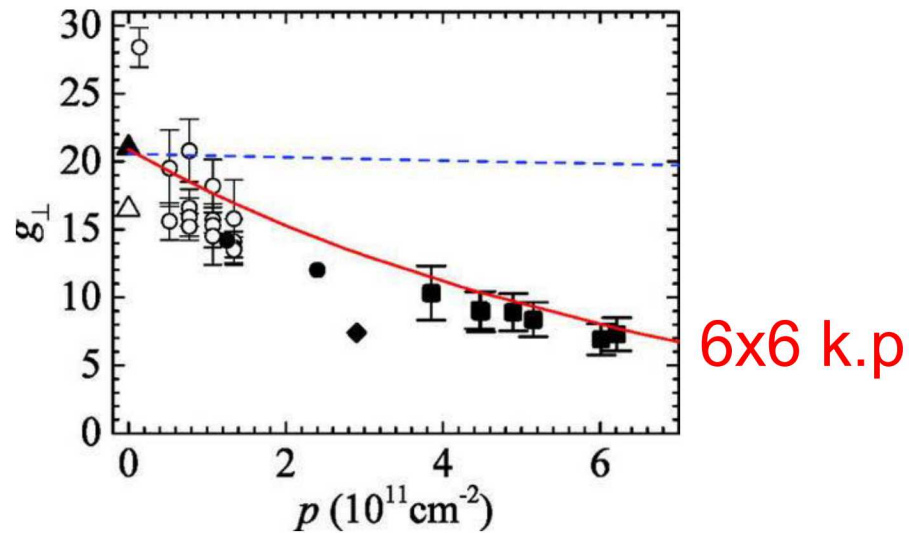


FIG. 8. Figures of constant energy in the (100) plane of k -space for the two fluted energy surfaces which are degenerate at the valence band edge; constants as for germanium.

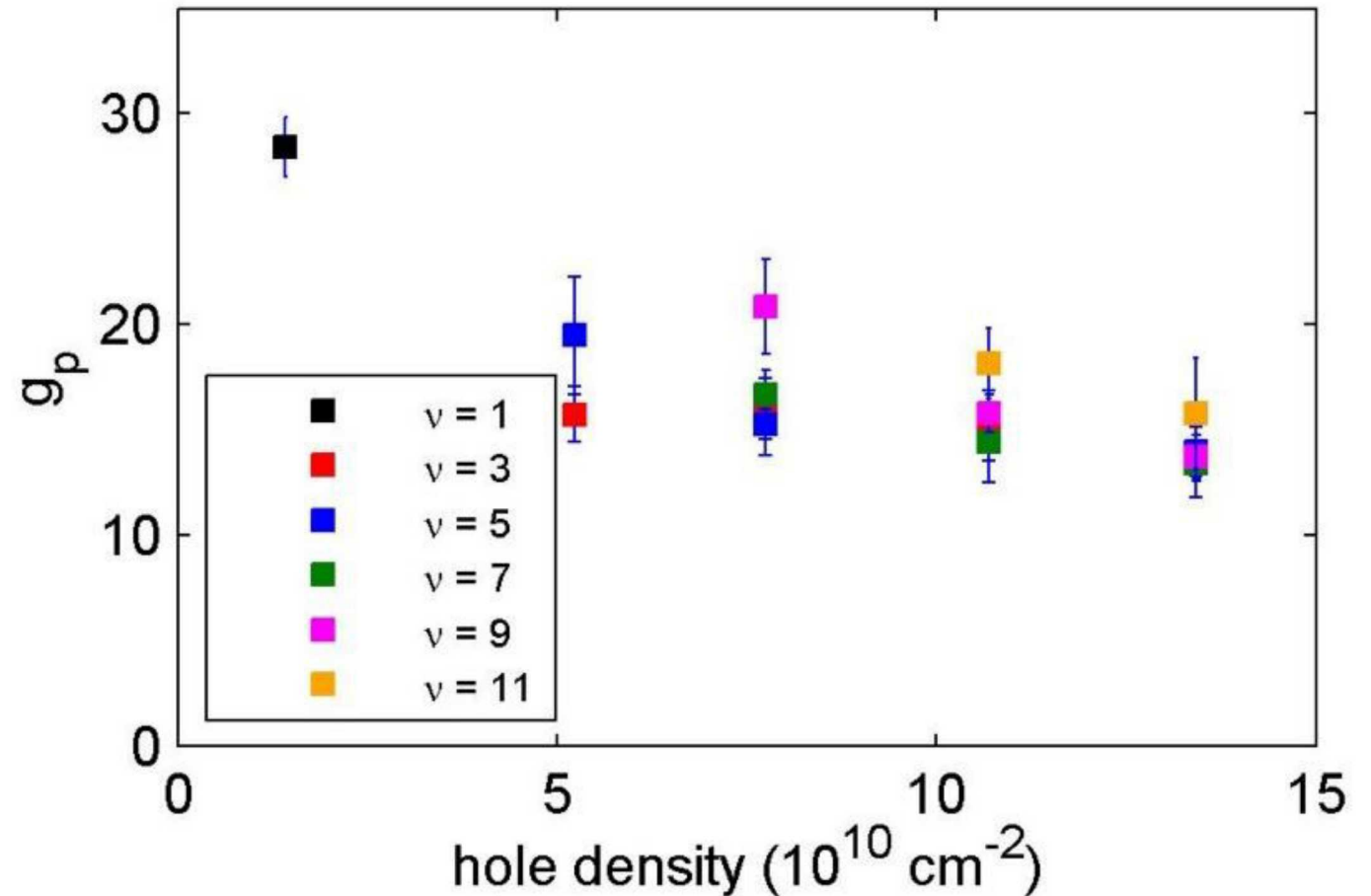
Physical properties – g factor (odd filling factors)

- $\sim 10 - 30$
- $\sim$ density dependent.
- The g factor is large compared to the g factor of electrons in Si (~ 2) and the g factor of electrons in GaAs (~ 0.44).



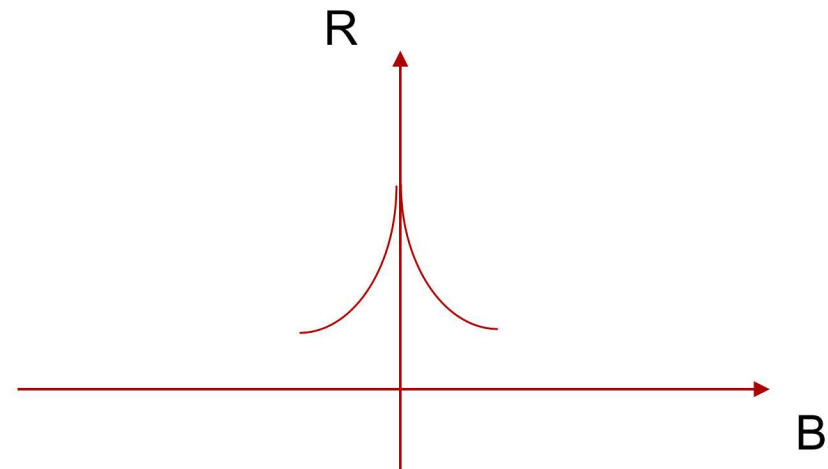
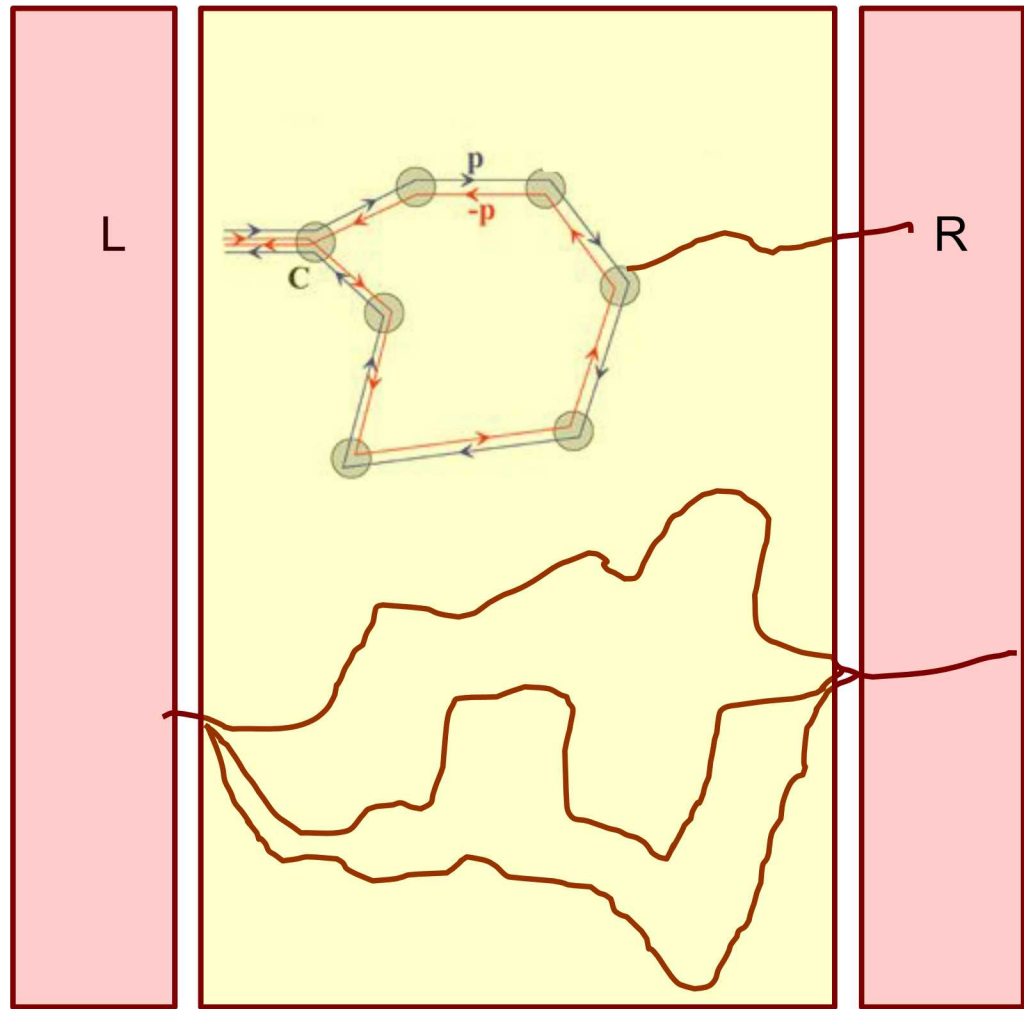
Drichko J. Appl. Phys. 123, 165703 (2018)

 Data from our work.



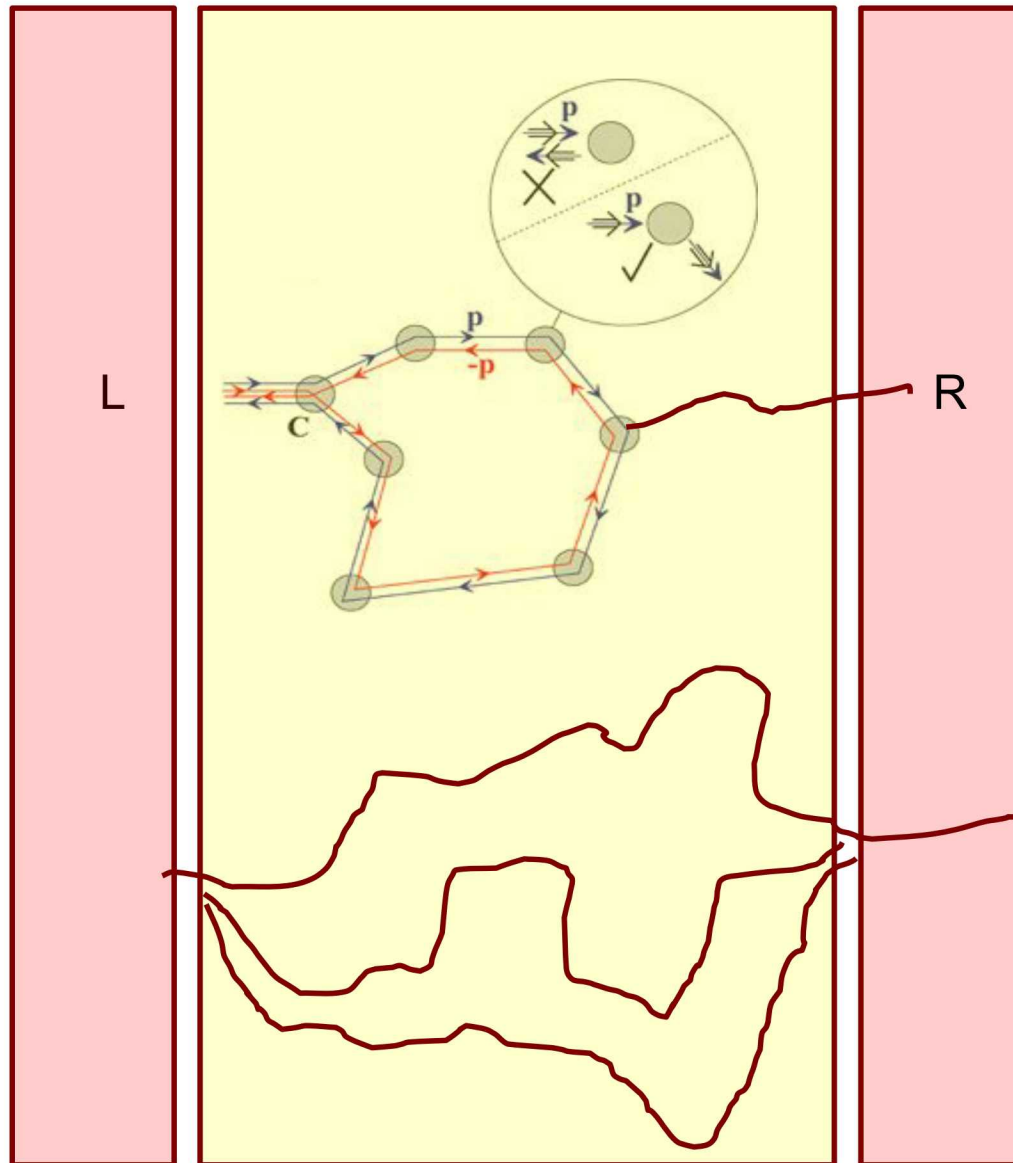
Lu, Appl. Phys. Lett. 111, 102108 (2017)

Weak localization (no spin-orbit coupling)

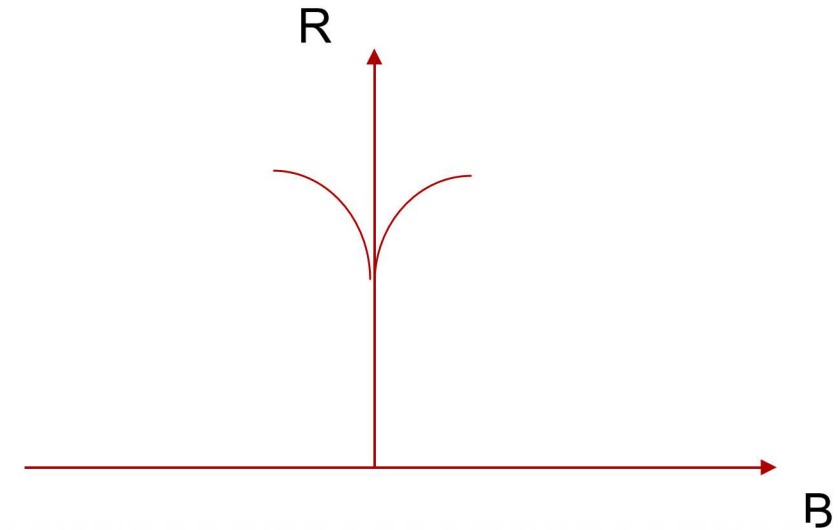


Adapted from McCann Physics 2, 98

Weak anti-localization (spin-orbit coupling)



Spin and momentum are locked together.
Back scattering is suppressed.



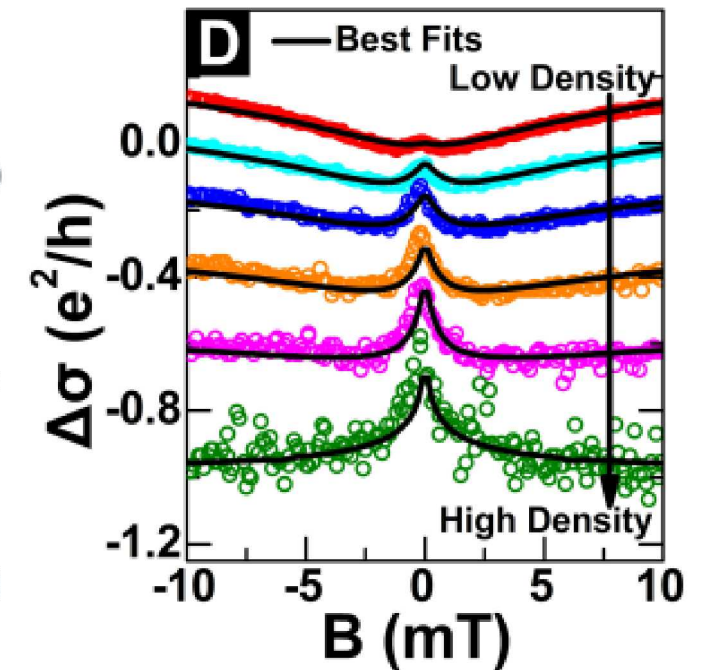
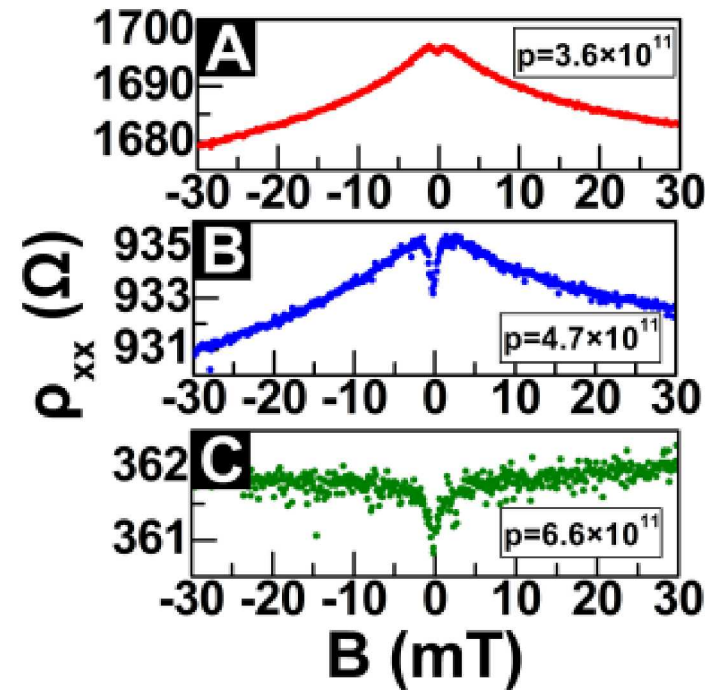
$$\Delta\sigma(B) - \Delta\sigma(0) = \frac{e^2}{2\pi^2\hbar} \left\{ \psi\left(\frac{1}{2} + \frac{H_\varphi}{B} + \frac{H_{SO}}{B}\right) + \frac{1}{2} \psi\left(\frac{1}{2} + \frac{H_\varphi}{B} + \frac{2H_{SO}}{B}\right) - \frac{1}{2} \psi\left(\frac{1}{2} + \frac{H_\varphi}{B}\right) - \ln \frac{H_\varphi + H_{SO}}{B} - \frac{1}{2} \ln \frac{H_\varphi + 2H_{SO}}{B} + \frac{1}{2} \ln \frac{H_\varphi}{B} \right\}$$

Hikami Prog. Theor. Phys. 63, 707

Adapted from McCann Physics 2, 98

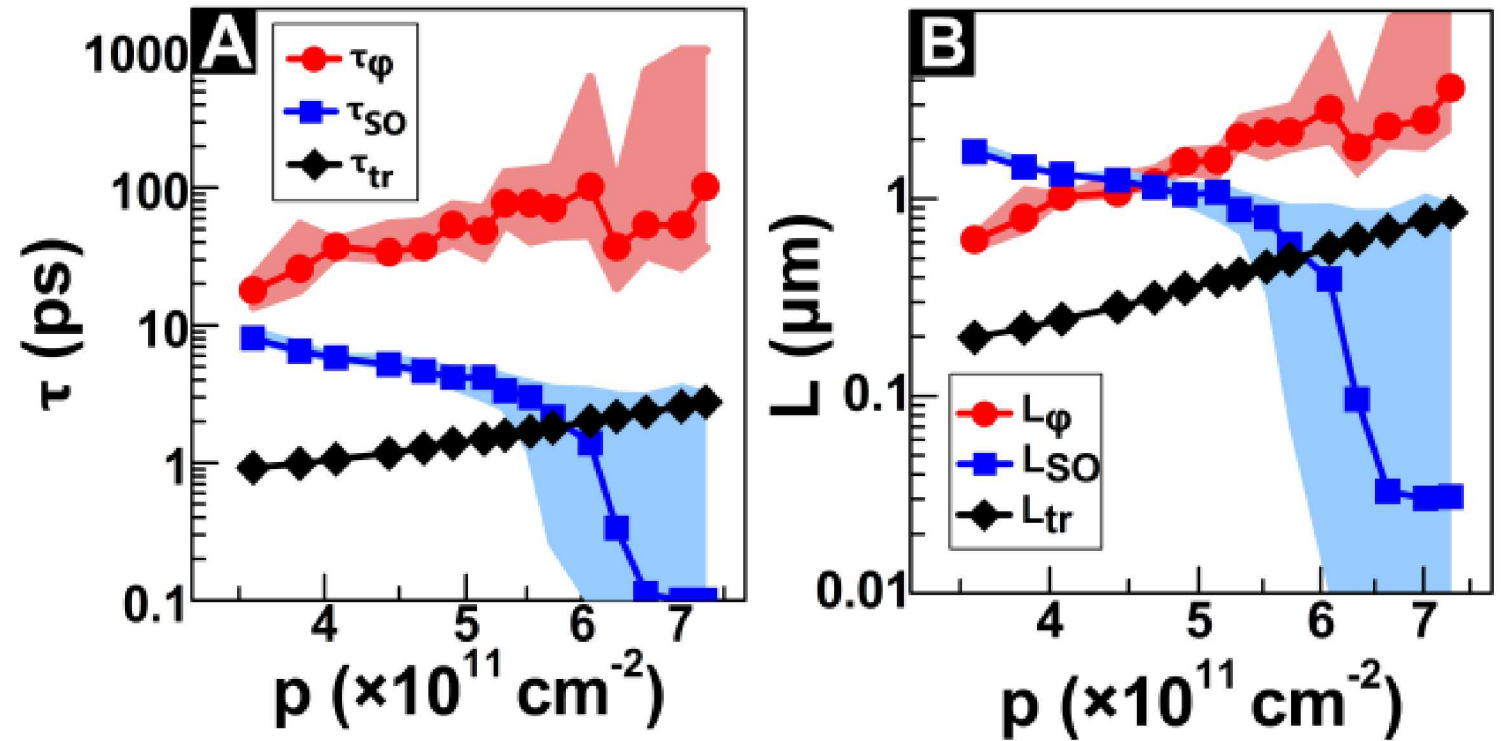
Physical properties – spin-orbit coupling

- Low densities
 - Weak localization only
- Intermediate densities
 - Weak anti-localization on top of weak localization only
- High densities
 - Weak anti-localization only



Physical properties – spin-orbit coupling

- Spin-orbit length decreases with density and can be as short as 0.1 μm ($<$ mean free path), while the phase coherence length can be a few microns long ($>$ mean free path)
- This means the hole spin can rotate at a high yet controlled rate, maintain its phase coherence, and suffer no scattering.



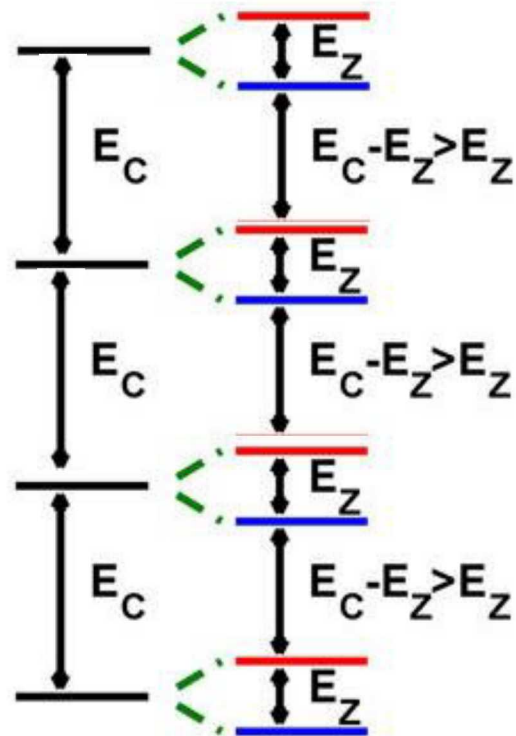
Physical properties – weak antilocalization beyond diffusive regime



- Conventional theories for weak (anti)localization are only valid in the diffusive regime at low magnetic fields.
- Our data lie outside this regime.
- Numerical methods and code for HPC available with paper.

The quantum Hall effect

In a perpendicular magnetic field, the spectrum of a 2D gas is a series of Landau levels:



E_C is cyclotron gap: $\hbar e B / (2\pi m^*)$

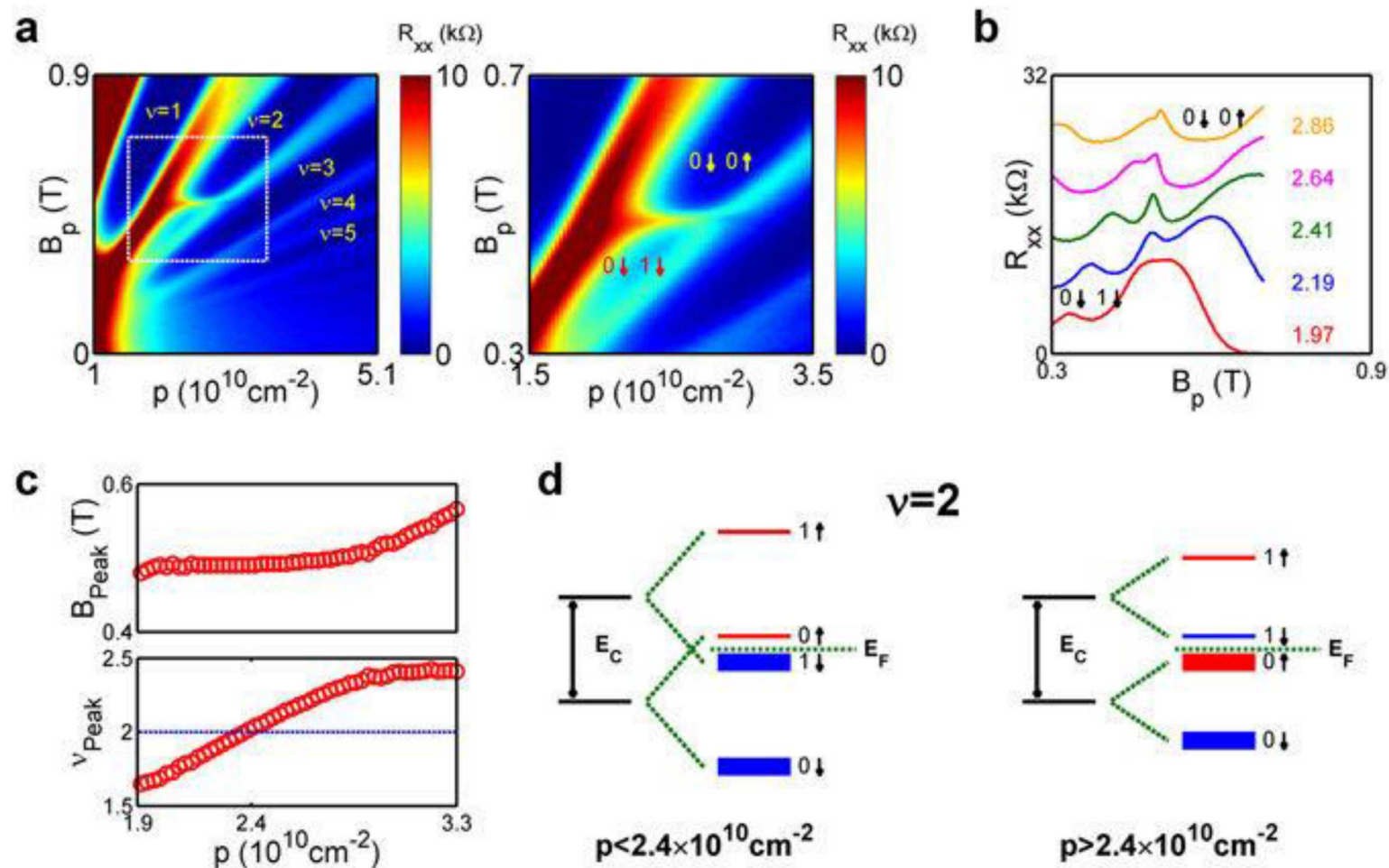
E_Z is Zeeman gap: $g^* \mu_B$

m^* and g^* are material parameters.

Landau level degeneracy (# electrons / area):
 eB/h



Quantum Hall ferromagnetic transition



A spin transition (unpolarized $\leftrightarrow$ polarized) at $\nu=2$ occurs at $p \sim 2.4 \times 10^{10}$ cm $^{-2}$.

This transition marks the point where $E_C \sim E_z$

$$\frac{\hbar e B}{(2\pi m^*)} = g^* \mu_B$$

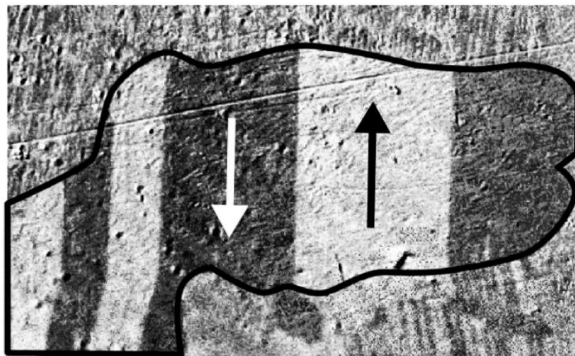
$$\Rightarrow m^* g^* = 2$$

Quantum Hall ferromagnetic transition

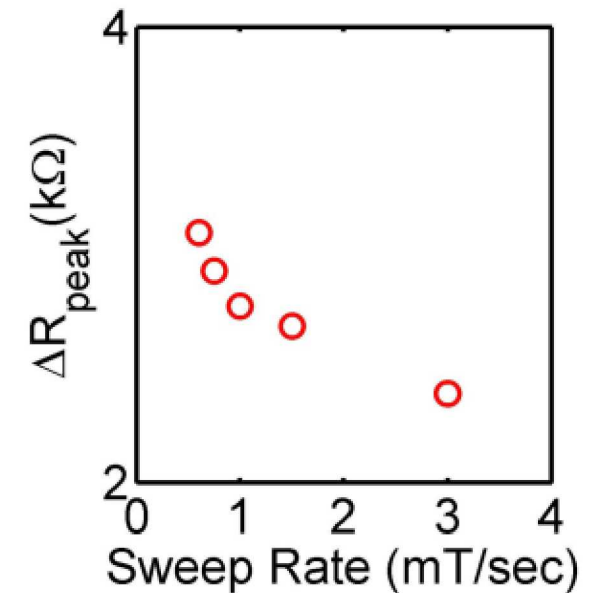
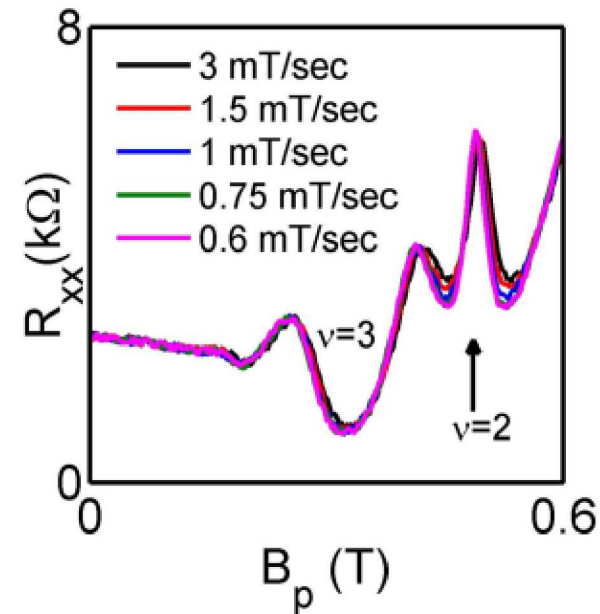
The physical picture of the system at the transition:

micro-domains of different spin configurations. Away from the transition, one spin configuration is preferred. Domains move and merge to minimize surface energy.

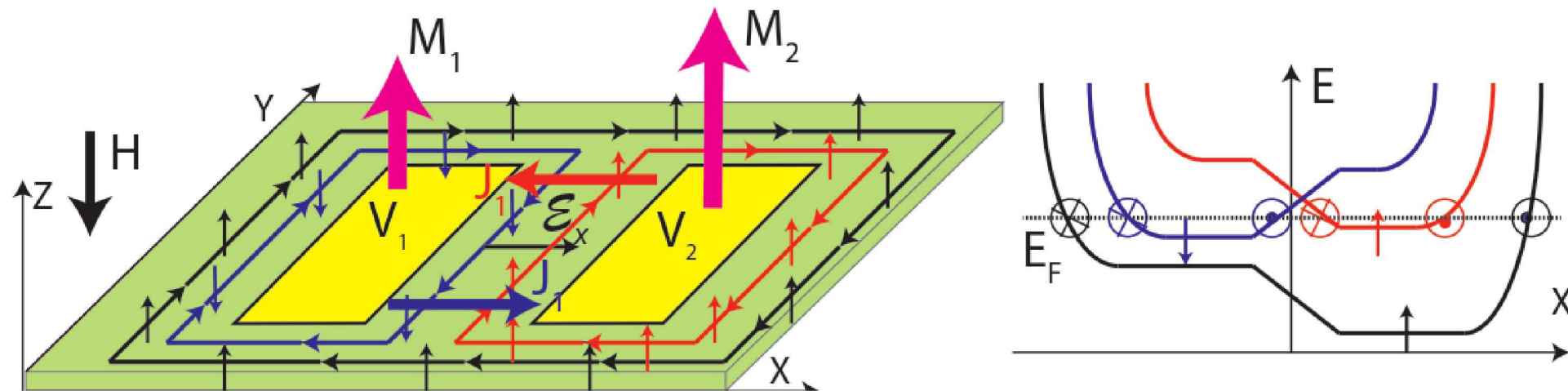
Evidence of micro-domains is found in the time dependence.



by S. Zurek, E. Magnetica, [CC-BY-3.0](#)



Local gating to create counter-propagating edge states with opposite spins



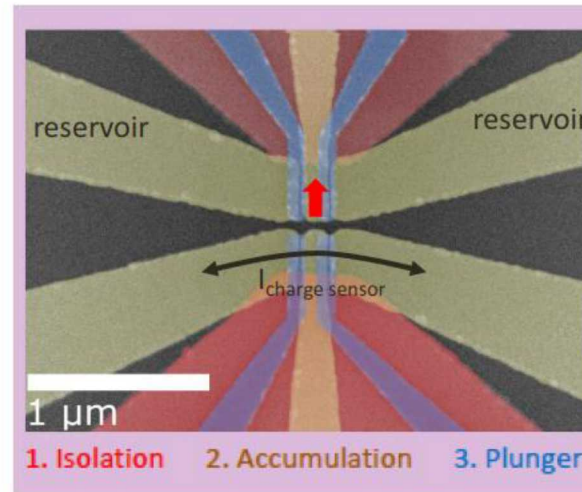
“Impurity-generated non-Abelions”
Simion Phys. Rev. B 97, 245107 (2018)

Implications for Quantum Dots

- Low Disorder
 - Help Dot-Dot Coupling
- Small Effective Mass
 - Help Dot-Dot coupling
 - Easier Lithography
- Anisotropic g-factor
 - Large g-factor allows operation at smaller magnetic fields
 - Dot-to-Dot variation is possible
- Strong Spin-Orbit-Coupling
 - Natural mechanism for qubit control
 - Introduces additional noise channel

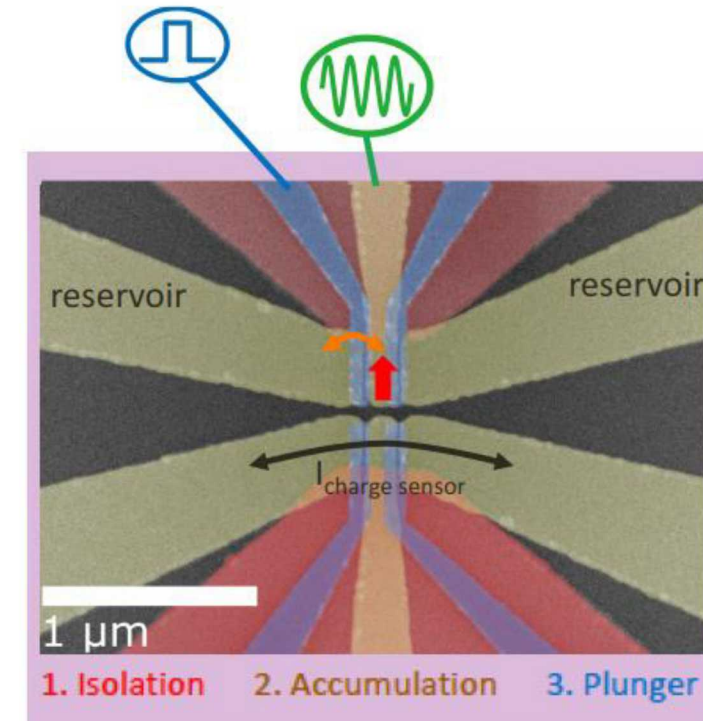
The effect of confinement on these properties remains largely unexplored

Surface electrodes used to laterally confine hole

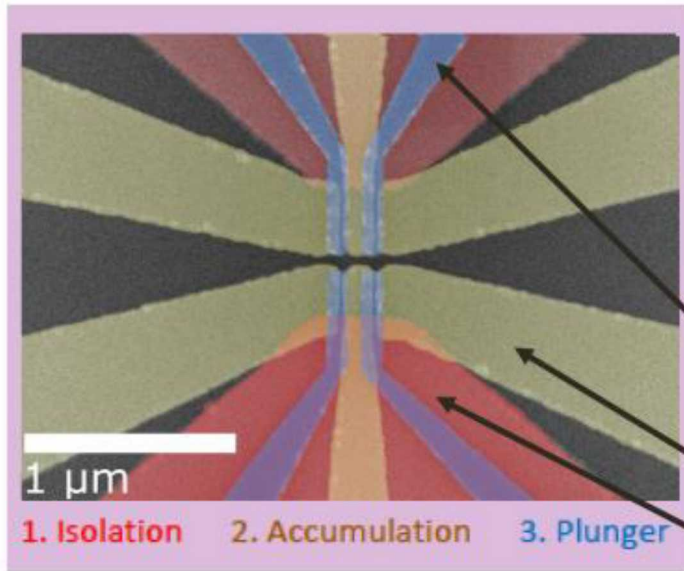


Spin qubits in Ge/SiGe

- Single Hole confined to lateral quantum dot
- Spin Qubit States: $m_j = \pm 3/2$
- Qubit readout and initialization through energy selective tunneling to reservoir
- Qubit Control through microwaves applied to gate
- Occupancy detected through nearby charge sensor



Spin qubits in Ge/SiGe

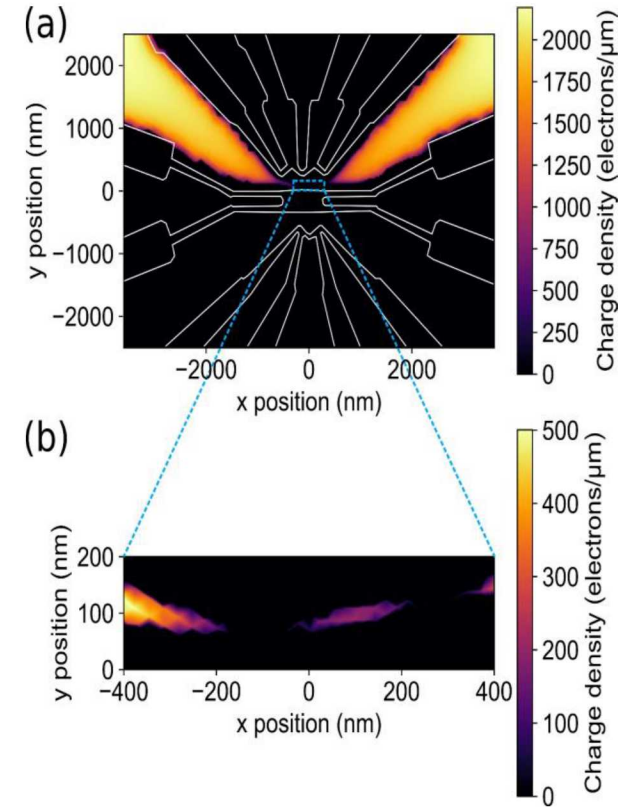


Ga implanted Ohmic contacts

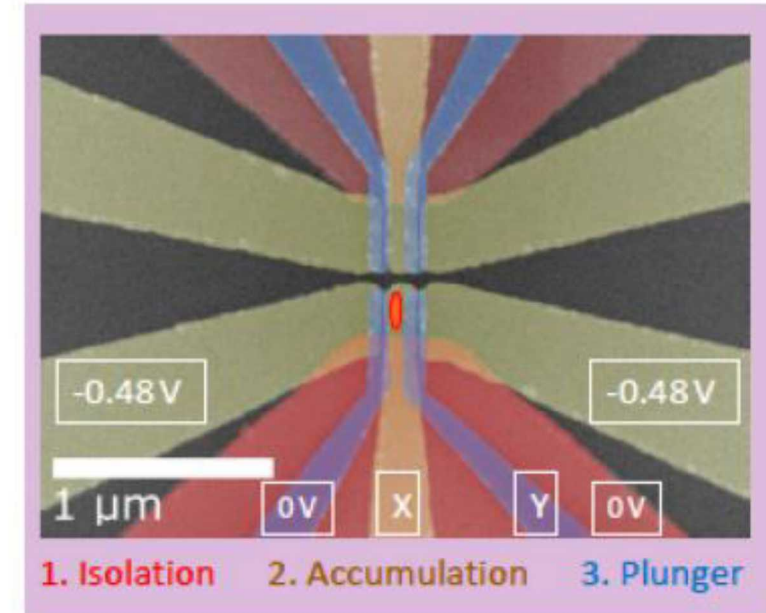
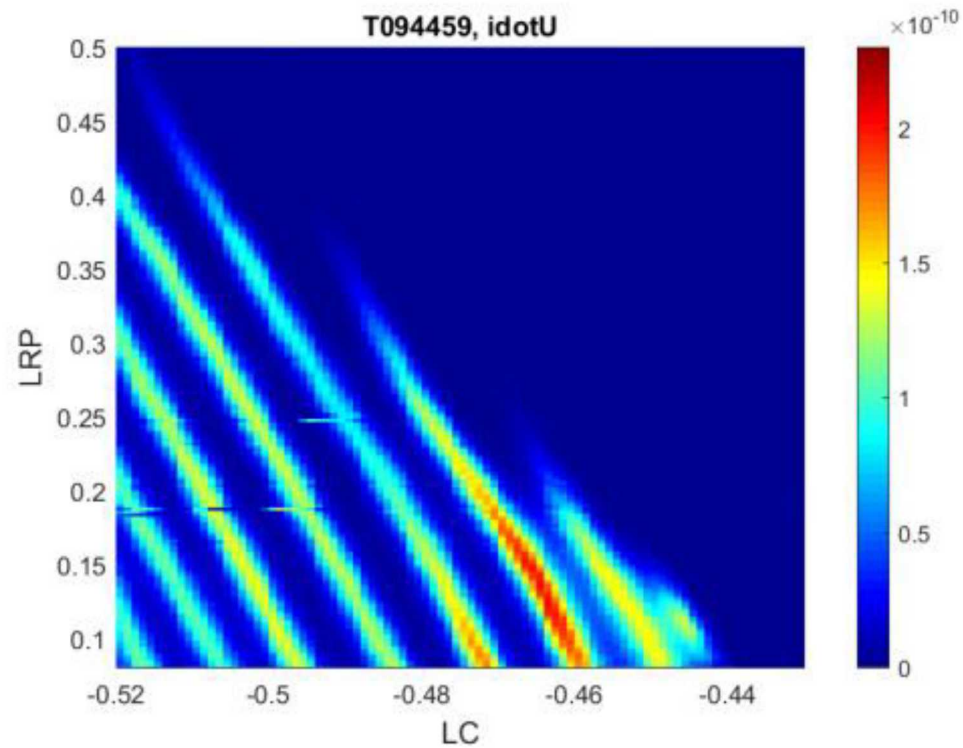
Goals:

- Independent Control of occupation and tunnel barriers
- Tighter Confinement
- Low Capacitance for EDSR





Three Metal Layer Device



Coulomb Blockade observed in
the three-metal-layer devices

Summary

- Induced 2D holes in Ge/SiGe heterostructure field effect transistors demonstrated.
- Device behavior can deviate from thermal equilibrium.
- Physical properties (mass, g factor, spin-orbit coupling strength) characterized.
- Gate controlled quantum Hall ferromagnetic transition observed at low densities. Platform for topological superconductivity?
- Development of spin qubits in Ge/SiGe